SGS-THOMSON MICROELECTRONICS

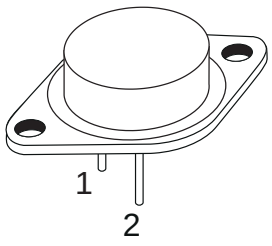
2N5038

HIGH CURRENT NPN SILICON TRANSISTOR

- SGS-THOMSON PREFERRED SALESTYPE
- NPN TRANSISTOR

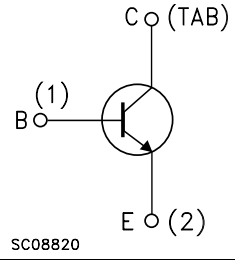
DESCRIPTION

The 2N5038 is a silicon planar multiepitaxial NPN transistors in Jedec TO-3 metal case. They are especially intended for high current and switching applications.



TO-3

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage (I_E = 0)	150	V
V_{CEX}	Collector-Emitter Voltage (V_{BE}=-1.5V R_{BE}=100Ω)	150	V
V_{CER}	Collector-Emitter Voltage (R_{BE} < 50Ω)	110	V
V_{CEO}	Collector-Emitter Voltage (I_B = 0)	90	V
V_{EBO}	Emitter-Base Voltage (I_C = 0)	7	V
I_C	Collector Current	20	A
I_{CM}	Collector Peak Current	30	A
I_B	Base Current	5	A
P_{tot}	Total Dissipation at $T_c \leq 25\ ^oC$	140	W
T_{stg}	Storage Temperature	-65 to 200	^oC
T_j	Max. Operating Junction Temperature	200	^oC

THERMAL DATA

$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	1.25	$^oC/W$

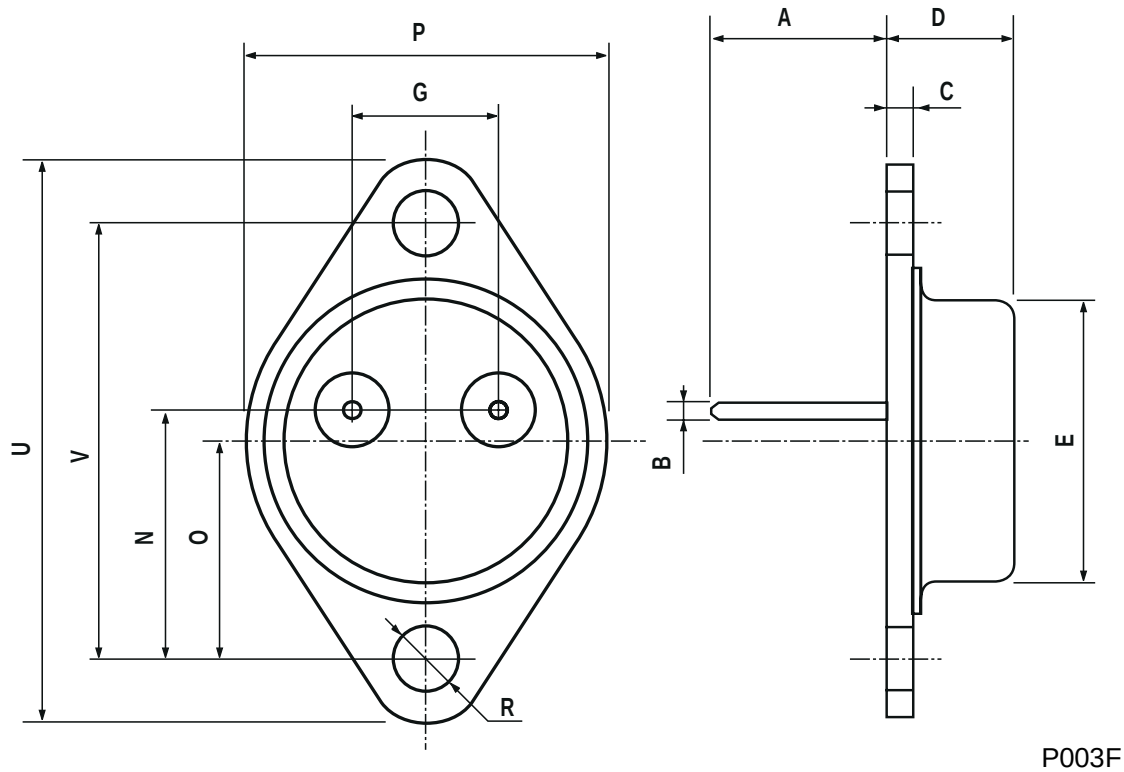
ELECTRICAL CHARACTERISTICS (T_{case} = 25 ^oC unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CEV}	Collector Cut-off Current (V_{BE} = -1.5V)	V_{CE} = 140 V V_{CE} = 100 V T_c = 150 ^oC			 50 10	 mA mA
I_{CEO}	Collector Cut-off Current (I_B = 0)	V_{CE} = 70 V			20	mA
I_{EBO}	Emitter Cut-off Current (I_C = 0)	V_{EB} = 7 V V_{EB} = 5 V			50 5	mA mA
$V_{CEO(sus)}$*	Collector-Emitter Sustaining Voltage	I_C = 0.2 A	90			V
$V_{CER(sus)}$*	Collector-Emitter Sustaining Voltage	I_C = 0.2 A R_{BE} = 50 Ω	110			V
$V_{CEX(sus)}$*	Collector-Emitter Sustaining Voltage	I_C = 0.2 A R_{BE} = 100 Ω V_{BE} =-1.5V	150			V
$V_{CE(sat)}$*	Collector-Emitter Saturation Voltage	I_C = 12 A I_B = 1.2 A I_C = 20 A I_B = 5 A			1 2.5	V V
$V_{BE(sat)}$*	Collector-Emitter Saturation Voltage	I_C = 20 A I_B = 5 A			3.3	V
V_{BE}*	Base-Emitter Voltage	I_C = 12 A V_{CE} = 5 V			1.8	V
h_{FE}*	DC Current Gain	I_C = 2 A V_{CE} = 5 V I_C = 12 A V_{CE} = 5 V	50 20		250 100	
h_{fe}	Small Signal Current Gain	I_C = 2 A V_{CE} = 10 V f = 5 MHz	12			
C_{CBO}	Collector-Base Capacitance	I_E = 0 V_{CB} = 10 V f = 1 MHz			300	pF
t_r	Rise Time	I_C = 12 A V_{CC} = 30 V I_{B1} = -I_{B2} = 1.2A			0.5	µs
t_s	Storage Time				1.5	µs
t_f	Fall Time				0.5	µs
$I_{s/b}$**	Second Breakdown Collector Current	V_{CE} = 28 V V_{CE} = 45 V	5 0.9			A A
$E_{s/b}$	Second Breakdown Energy	V_{BE} = -4 V R_{BE} = 20 Ω L = 180µH	13			mJ

* Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

TO-3 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.00		13.10	0.433		0.516
B	0.97		1.15	0.038		0.045
C	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
E	19.00		20.00	0.748		0.787
G	10.70		11.10	0.421		0.437
N	16.50		17.20	0.649		0.677
P	25.00		26.00	0.984		1.023
R	4.00		4.09	0.157		0.161
U	38.50		39.30	1.515		1.547
V	30.00		30.30	1.187		1.193



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